



PATENT
Customer No. 22,852
Attorney Docket No. 02887.0141-01

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Yukihito OOWAKI et al.

Application No.: 09/879,208

Filed: June 13, 2001

For: MIS TRANSISTOR AND METHOD
FOR PRODUCING THE SAME

Group Art Unit: 2814

Examiner: S. Rao

#6/B
3/22/2
Muller

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Commissioner for Patents
Washington, DC 20231

Sir:

AMENDMENT

In reply to the Office Action dated December 14, 2001, please amend the
application as follows:

IN THE CLAIMS:

Please cancel claims 10-13, and add new claims 14-39, as follows:

03/22/2002 SSURLES

01 FC:102
02 FC:103

00000001 04/16 (New) A method for producing a MIS transistor comprising a
semiconductor substrate, source/drain regions formed on the semiconductor substrate,
and a gate electrode provided above a channel region between the source/drain
regions, said method comprising:

selectively forming a first film on said semiconductor substrate;

etching said semiconductor substrate to form a first groove by using said first film

as a mask;

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